

## **N-Channel Power MOSFET**

800V, 0.3A, 21.6Ω

#### **FEATURES**

- Advanced planar process
- 100% avalanche tested
- Fast switching

### **APPLICATION**

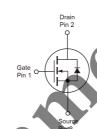
- Power Supply
- Lighting

KEY PERFORMANCE PARAMETERS			
PARAMETER	TER VALUE UNIT		
V <sub>DS</sub>	800	V	
R <sub>DS(on)</sub> (max)	21.6	Ω	
$Q_g$	5	nC	









Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	800	V
Gate-Source Voltage	V <sub>GS</sub>	±30	V
Continuous Drain Current	I <sub>D</sub>	0.3	Α
Pulsed Drain Current (Note 1)	I <sub>DM</sub>	1	А
Single Pulse Avalanche Energy (Note 2)	E <sub>AS</sub>	90	mJ
Avalanche Current, Repetitive or Not-Repetitive (Note 1)	I <sub>AR</sub>	1	А
Total Power Dissipation @ T <sub>C</sub> = 25°C	P <sub>DTOT</sub>	2.1	W
Operating Junction Temperature	T <sub>J</sub>	150	°C
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Ambient Thermal Resistance	R <sub>⊖JA</sub>	60	°C/W	

**Notes:**  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JA}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.  $R_{\Theta JA}$  shown below for single device operation on FR-4 PCB in still air



<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$ , $I_D = 1mA$	BV <sub>DSS</sub>	800			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 0.15A$	R <sub>DS(ON)</sub>		18	21.6	Ω
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	3		5	V
Zero Gate Voltage Drain Current	$V_{DS} = 800V, V_{GS} = 0V$	I <sub>DSS</sub>			25	μA
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I <sub>GSS</sub>		🗸	±10	μA
Forward Transconductance	$V_{DS} = 40V, I_{D} = 0.1A$	g <sub>fs</sub>		0.36		S
Diode Forward Voltage	$I_S = 0.2A, V_{GS} = 0V$	V <sub>SD</sub>			1.4	V
Dynamic (Note 3)			7			
Total Gate Charge		$Q_g$		.5	6	
Gate-Source Charge	$V_{DS} = 640V, I_{D} = 0.3A,$	$Q_{gs}$		1		nC
Gate-Drain Charge	$V_{GS} = 10V$	Q <sub>gd</sub>		2		
Input Capacitance		C <sub>iss</sub>		155	200	
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	Coss		20	26	pF
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>		2.7	4	
Switching (Note 4)						
Turn-On Delay Time		t <sub>d(on)</sub>		10	30	
Turn-On Rise Time	$V_{GS} = 10V, I_D = 0.3A,$	t <sub>r</sub>		20	50	
Turn-Off Delay Time	$V_{DS} = 400V, R_G = 25\Omega$	t <sub>d(off)</sub>		16	45	ns
Turn-Off Fall Time		t <sub>f</sub>		25	60	

## Note:

- 1. Pulse test: pulse width <=300uS, duty cycle <=2%
- 2.  $(V_{DD} = 50V, I_{AS}=0.8A, L=170mH, R_{G}=25Q)$
- 3. For design reference only, not subject to production testing.
- 4. Switching time is essentially independent of operating temperature.



### **ORDERING INFORMATION**

PART NO.	PACKAGE	PACKING
TSM1N80CW RPG	SOT-223	2,500pcs / 13" Reel

#### Note:

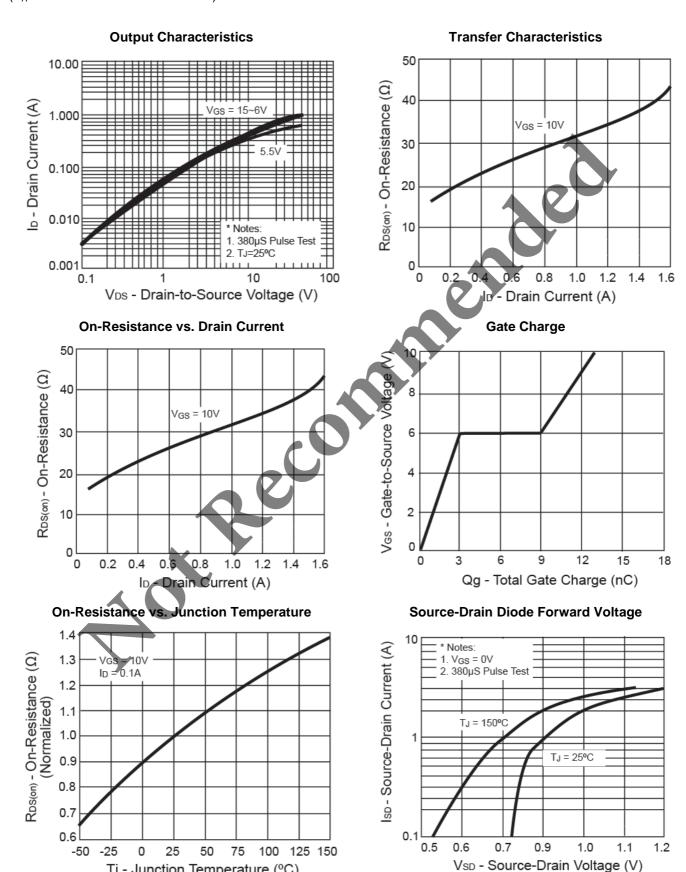
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- 2. Halogen-free according to IEC 61249-2-21 definition





### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

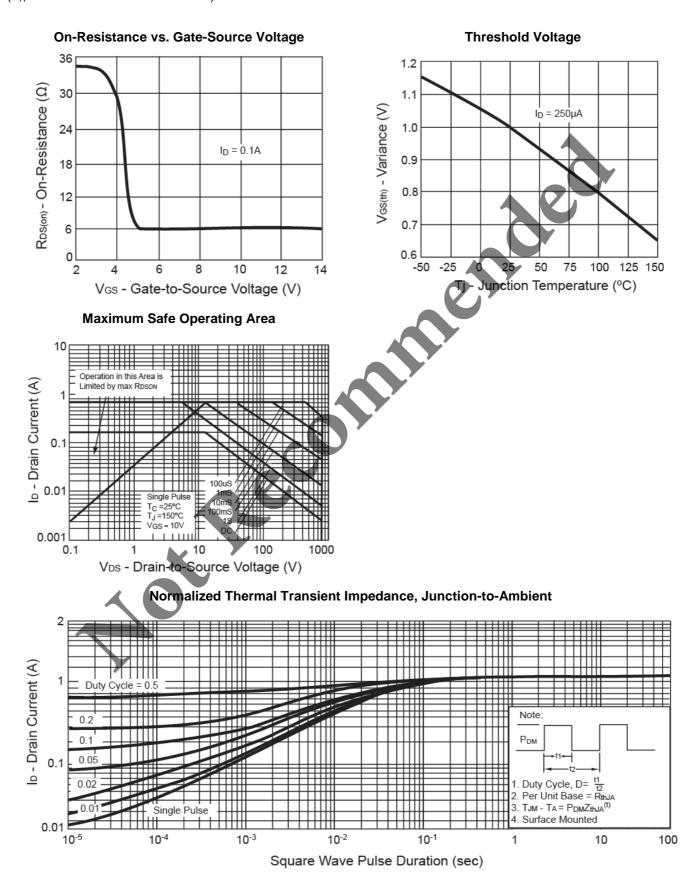


Tj - Junction Temperature (°C)



### **CHARACTERISTICS CURVES**

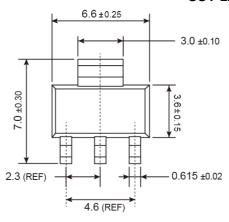
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

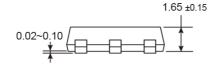




## PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

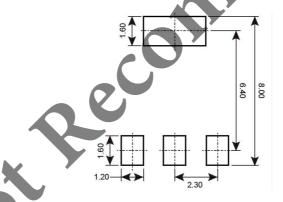
### **SOT-223**



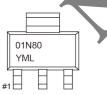




## **SUGGESTED PAD LAYOUT (Unit: Millimeters)**



# **MARKING DIAGRAM**



Y = Year Code

**M** = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S = May T = Jun U = Jul V = Aug

W = Sep X = Oct Y = Nov Z = Dec

L = Lot Code (1~9, A~Z)





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